



N 沟道增强型场效应晶体管
N-CHANNEL MOSFET

MC10N020

主要参数 MAIN CHARACTERISTICS

ID	45A
V _{DSS}	100V
R _{dson-typ} (@V _{gs} =10V)	17mΩ
Q _{g-typ}	21nC

用途

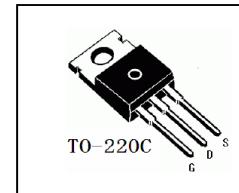
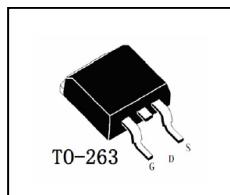
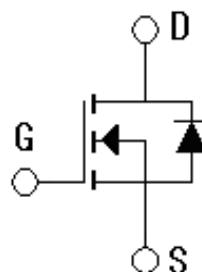
- 高功率 DC/DC 转换与功率开关
 - 同步整流领域 DC/DC 与 AC/DC 转换
 - 直流电机控制
- High power DC/DC Converters and switch mode power supplies
 - Synchronous Rectification in DC/DC and AC/DC Converters
 - DC Motor Control

产品特性

- 低栅极电荷
 - 低 R_{dson}
 - 开关速度快
 - 产品全部经过雪崩测试
 - 高可靠性
 - RoHS 产品
- Low gate charge
 - Low R_{dson}
 - Fast switching
 - 100% avalanche tested
 - Highest reliability
 - RoHS product

FEATURES

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
MC10N020-C-B	MC10N020-C-BR	N/A	N/A	MC10N020	TO-220C
MC10N020-S-B	MC10N020-S-BR	MC10N020-S-A	MC10N020-S-AR	MC10N020	TO-263



MC10N020

绝对最大额定值 ABSOLUTE RATINGS (T_c=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		MC10N020	
最高漏极—源极直流电压 Drain-Source Voltage	V _{DSS}	100	V
连续漏极电流 Drain Current -continuous	I _D T=25°C	45*	A
	I _D T=100°C	29*	A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	I _{DM}	180*	A
最高栅源电压 Gate-Source Voltage	V _{GSS}	±20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E _{AS}	130	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I _{AS}	23	A
耗散功率 Power Dissipation	P _D T _c =25°C -Derate above 25°C	96	W
		0.77	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300	°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature



MC10N020

电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最 小 Min	典 型 Typ	最 大 Max	单 位 Units
关态特性 Off -Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	100	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS} = 20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS} = -20V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2	2.7	4	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=20A$	-	17	20	$m\Omega$
正向跨导 Forward Transconductance	g_{fs}	$V_{DS} = 5V, I_D=50A$ (note 4)	-	30	-	S
动态特性 Dynamic Characteristics						
栅电阻 Gate resistance	R_g	$f=1.0MHz, open drain$	-	1.5	-	Ω
输入电容 Input capacitance	C_{iss}	$V_{DS}=50V,$ $V_{GS} = 0V,$ $f=1.0MHz$	-	1400	-	pF
输出电容 Output capacitance	C_{oss}		-	175	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	7	-	pF



电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	t _{d(on)}	V _{DD} =50V, V _{GS} =10V I _D =30A, R _G =5.0Ω, (note 3, 4)	-	11	-	ns	
上升时间 Turn-On rise time	t _r		-	60	-	ns	
延迟时间 Turn-Off delay time	t _{d(off)}		-	17	-	ns	
下降时间 Turn-Off Fall time	t _f		-	57	-	ns	
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V I _D =30A (note 3, 4)	-	21	-	nC	
栅一源电荷 Gate-Source charge	Q _{gs}		-	10	-	nC	
栅一漏电荷 Gate-Drain charge	Q _{gd}		-	3.7	-	nC	
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流	I _s	T _C =25°C	-	-	45	A	
Maximum Continuous Drain -Source Diode Forward Current							
正向最大脉冲电流	I _{SM}	T _C =25°C	-	-	180	A	
Maximum Pulsed Drain-Source Diode Forward Current							
正向压降	V _{SD}	T _J =25°C, V _{GS} =0V, I _{SD} =20A	-	0.9	1.3	V	
Drain-Source Diode Forward Voltage							
反向恢复时间	T _{rr}	V _{GS} =0V, I _S =30A dI/dt=100A/μs (note 4)		55		ns	
Reverse recovery time							
反向恢复电荷	Q _{rr}			100		nc	
Reverse recovery charge							

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最 大 Max		单 位 Unit
		MC10N020		
结到管壳的热阻 Thermal Resistance, Junction to Case	R _{th(j-c)}	1.50		°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	R _{th(j-A)}	62.5		°C/W

注释:

1: 脉冲宽度由最高结温限制

Notes:

1: Pulse width limited by maximum junction temperature

2: I_{AS}=23A, V_{DD}=50V, V_{GS} =10V,L=0.5mH, R_G=25Ω,起始结温 T_J=25°C2: I_{AS}=23A, V_{DD}=50V, V_{GS} =10V,L=0.5mH, R_G=25Ω ,Starting T_J=25°C

3: 脉冲测试: 脉冲宽度≤300μs,占空比≤2%

3: Pulse Test: Pulse Width ≤300μs,Duty Cycle≤2%

4: 基本与工作温度无关

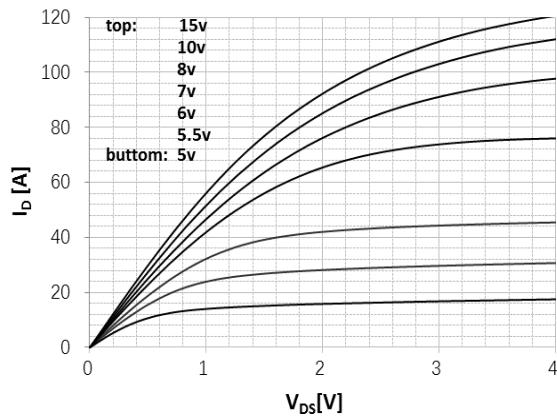
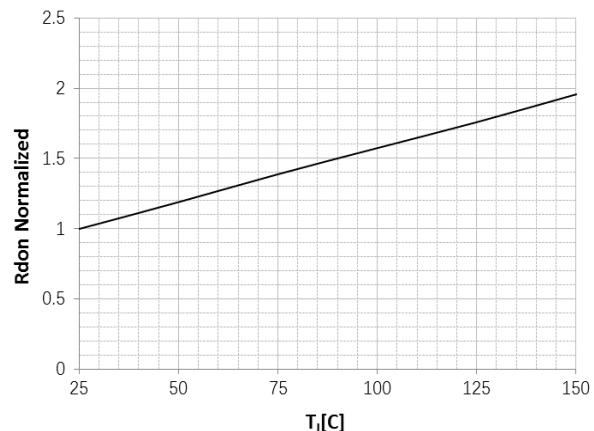
4: Essentially independent of operating temperature



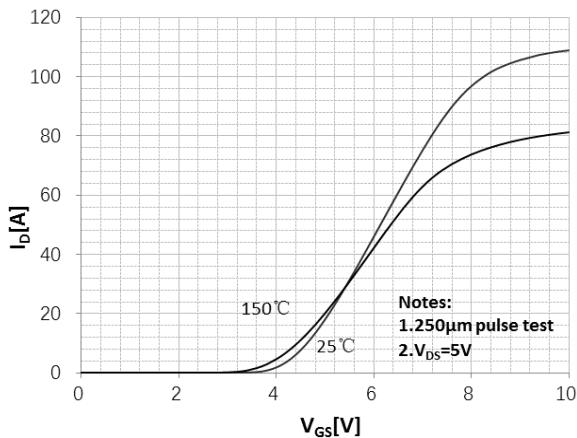
MC10N020

特征曲线 ELECTRICAL CHARACTERISTICS (curves), $T_J = 25^\circ\text{C}$

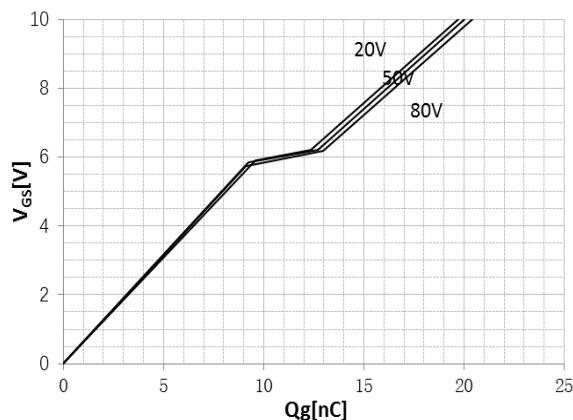
On-Region Characteristics

RDSON vs. T_J 

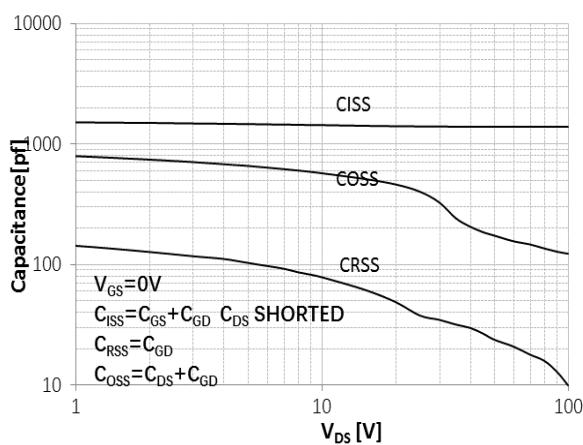
Transfer Characteristics



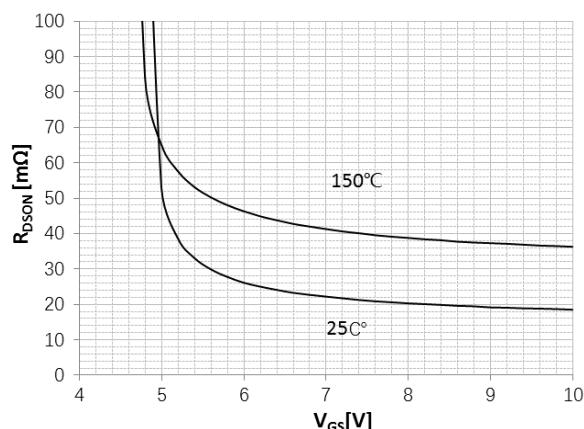
Gate Charge Characteristics

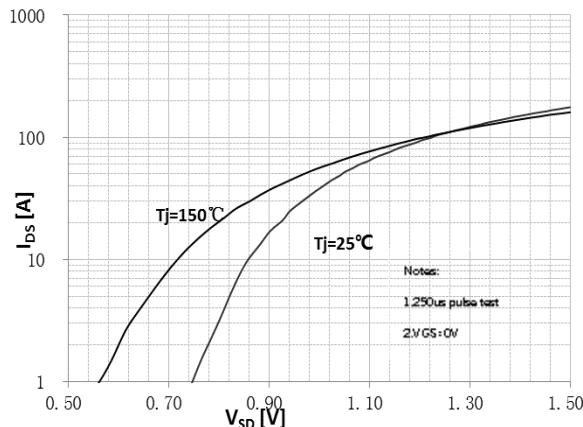
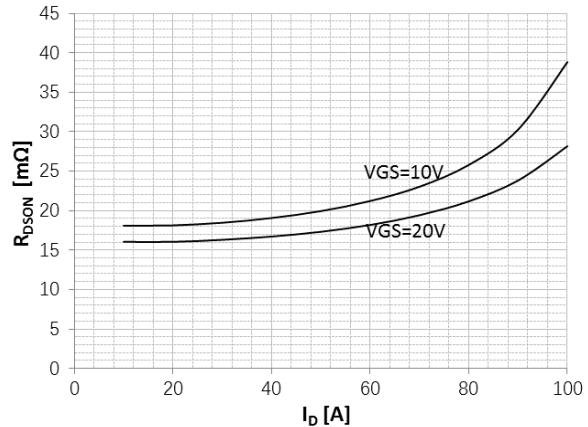
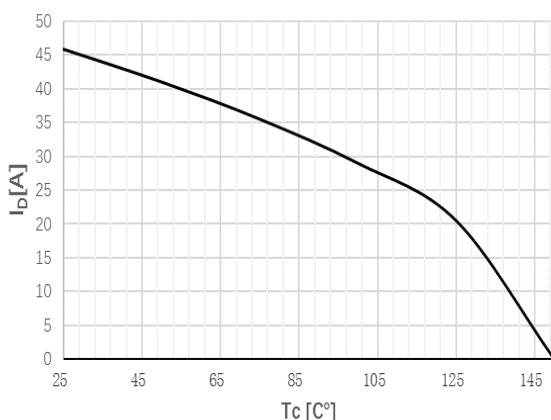
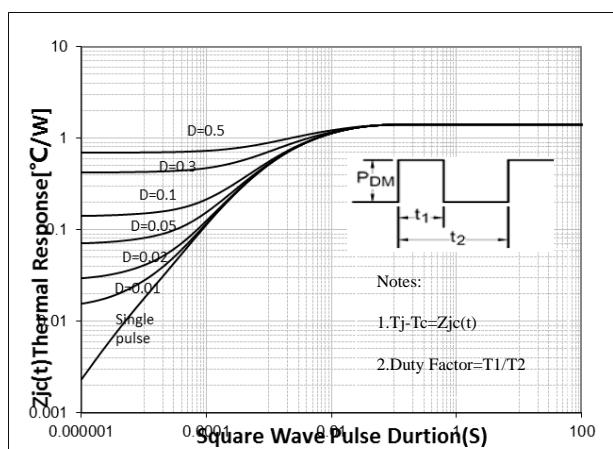
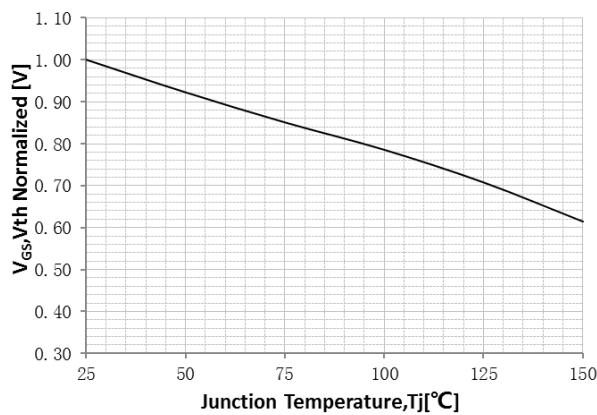
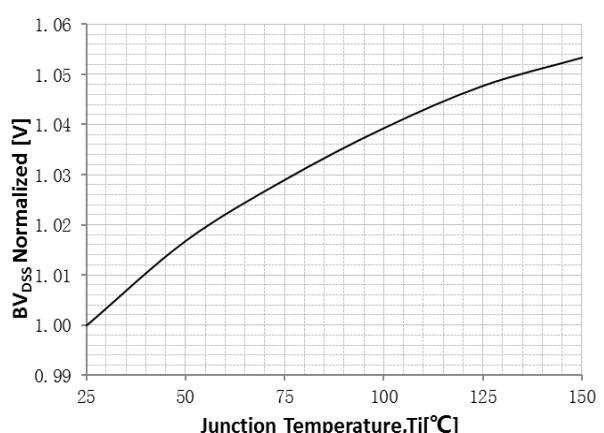


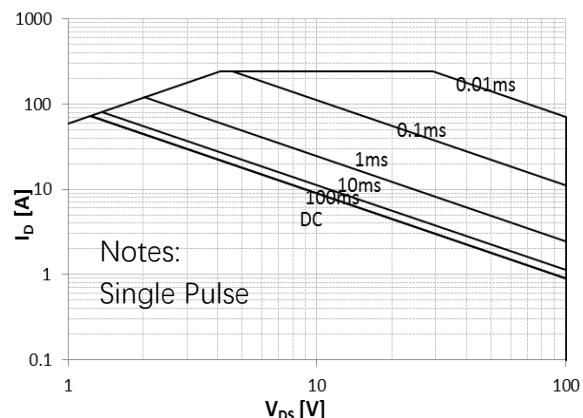
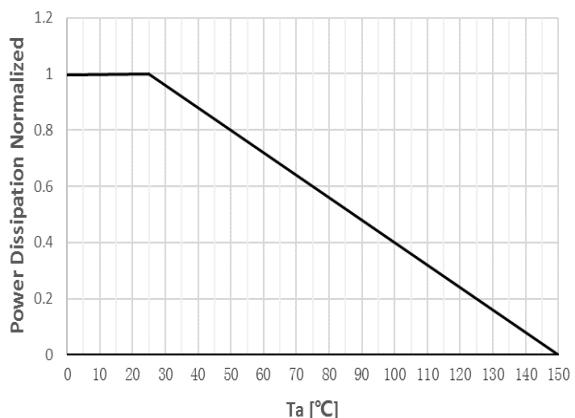
Capacitance Characteristics



Drain-Source on resistance



Body Diode Forward Voltage Variation vs. Source Current and Temperature

On-Resistance Variation vs. Drain Current and Gate Voltage

Drain Current Dissipation vs Tc

Transient Thermal Impedance

Gate Threshold Voltage Variation vs Tj

Breakdown Voltage Variation vs Tj


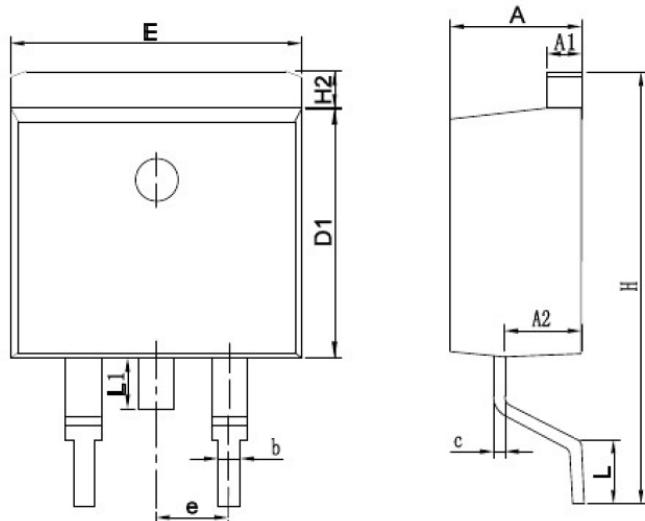
Maximum Safe Operation**Power Dissipation vs Ta**



外形尺寸 PACKAGE MECHANICAL DATA

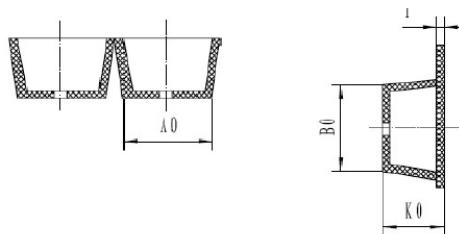
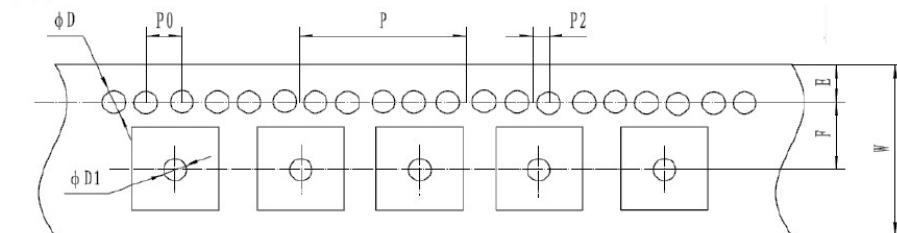
TO-263

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.28	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54 BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70

编带 REEL

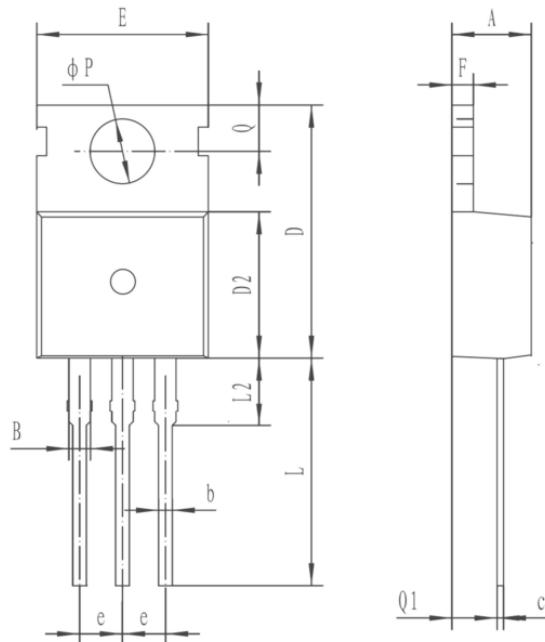


产品尺寸规格 (UNIT:mm)

规格	W	A0	E	F	D
尺寸	24 ± 0.3	10.9 ± 0.1	1.75 ± 0.1	11.5 ± 0.1	1.5 +0.1/-0
规格	D1	P0	P2	P	T
尺寸	1.5 +0.1/-0	4 ± 0.1	2 ± 0.1	16 ± 0.1	0.35 ± 0.05
规格	K0	B0			
尺寸	4.9 ± 0.1	16.0 ± 0.1			

外形尺寸 PACKAGE MECHANICAL DATA

TO-220C



符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80





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